

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ max}$	$I_D \text{ max}$ $T_A = +25^\circ\text{C}$
-60V	28m $\Omega$ @ $V_{GS} = -10\text{V}$	-7A
	35m $\Omega$ @ $V_{GS} = -4.5\text{V}$	-6.2A

## Description and Applications

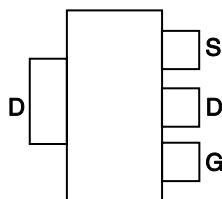
This MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

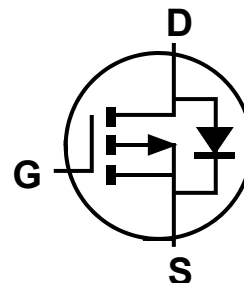
SOT223



Top View



Pin Out - Top View



Equivalent Circuit

## Features and Benefits

- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Low Input Capacitance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.  
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe.  
Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.112 grams (Approximate)

## Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMP6023LE-13	Standard	SOT223	2,500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



D = Manufacturer's Marking  
 P6023 = Marking Code  
 YWW = Date Code Marking  
 Y or Y = Year (ex: 4 = 2014)  
 WW = Week (01 - 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V <sub>DSS</sub>	-60	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = -10V	T <sub>A</sub> = +25°C	I <sub>D</sub>	-7	A
	T <sub>A</sub> = +70°C		-5.6	
	T <sub>C</sub> = +25°C	I <sub>D</sub>	-18.2	A
	T <sub>C</sub> = +70°C		-14.5	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)		I <sub>DM</sub>	-50	A
Maximum Continuous Body Diode Forward Current (Note 5)		I <sub>S</sub>	-2	A
Avalanche Current, L = 0.1mH		I <sub>AS</sub>	-35.5	A
Avalanche Energy, L = 0.1mH		E <sub>AS</sub>	62.9	mJ

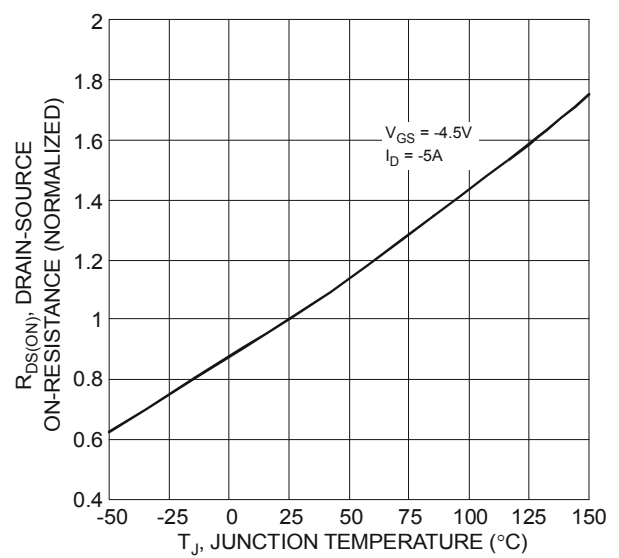
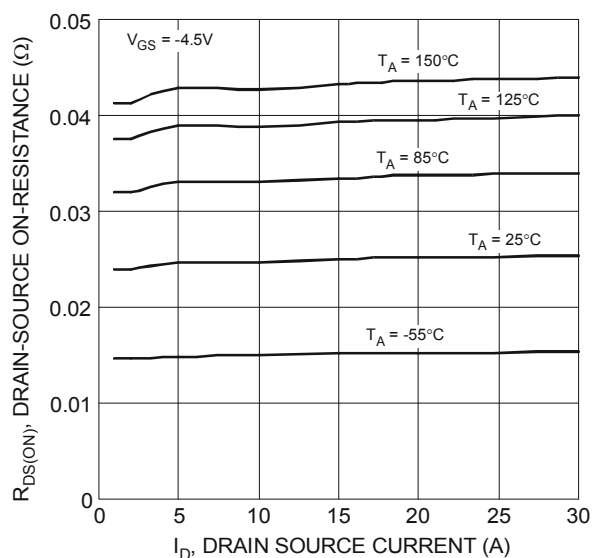
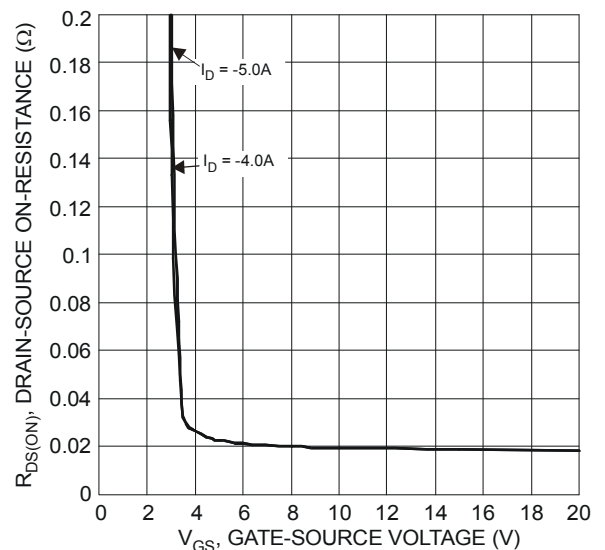
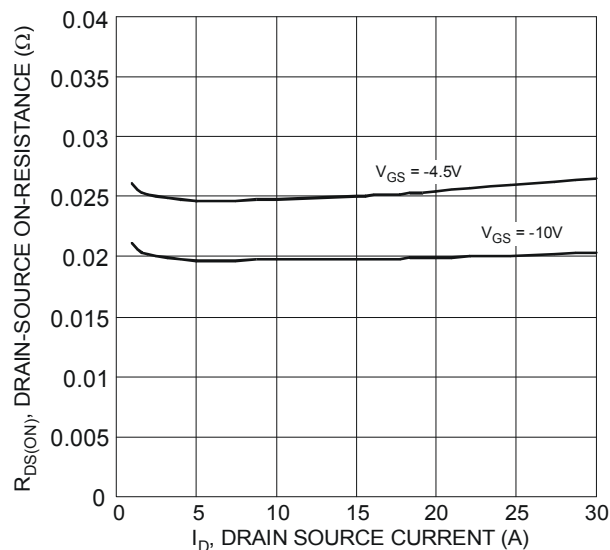
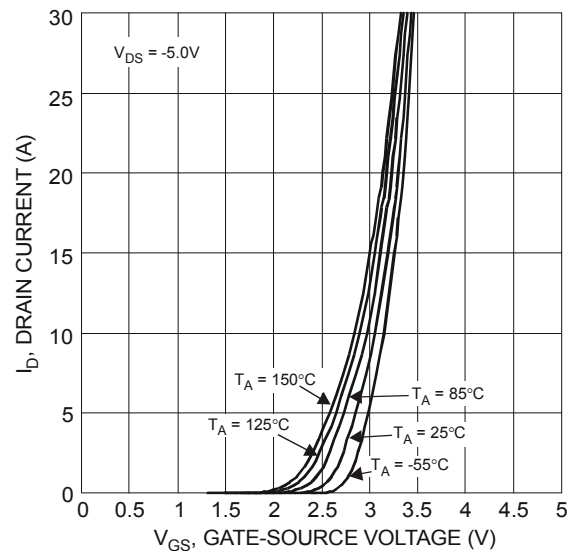
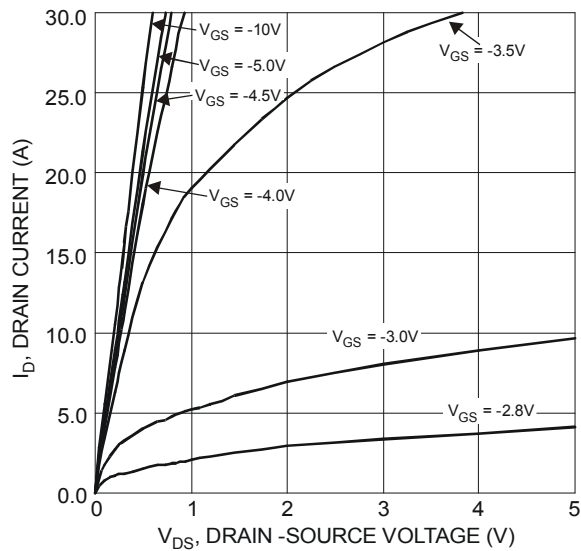
**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

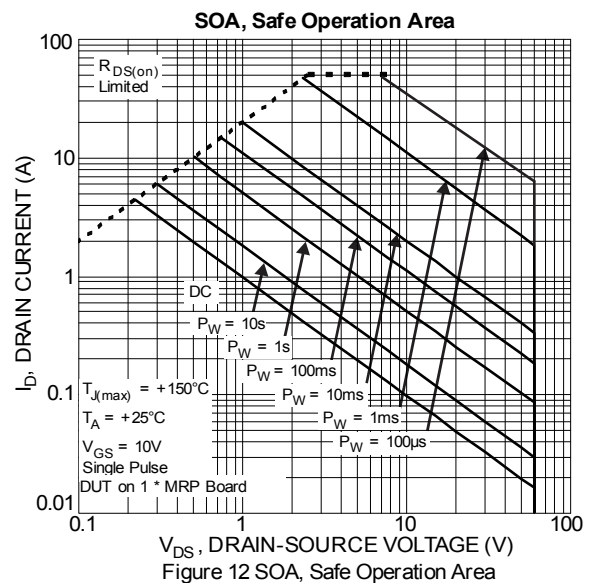
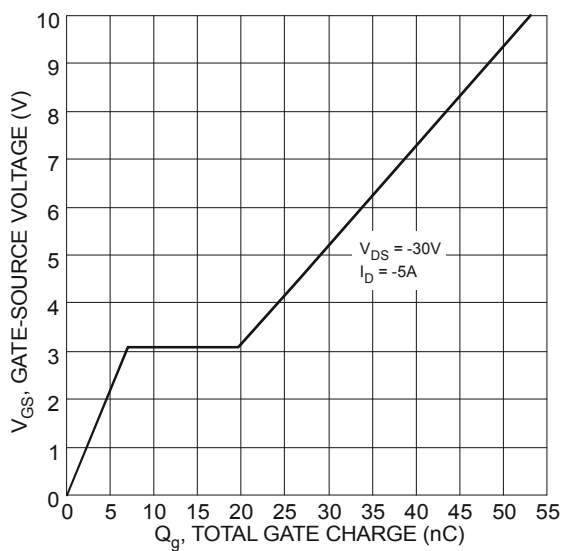
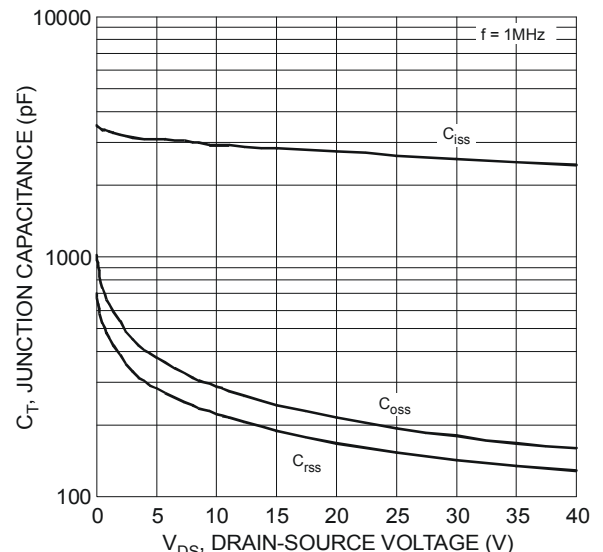
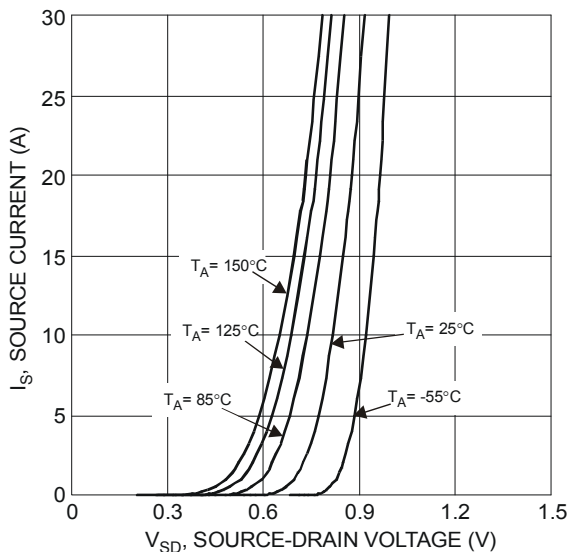
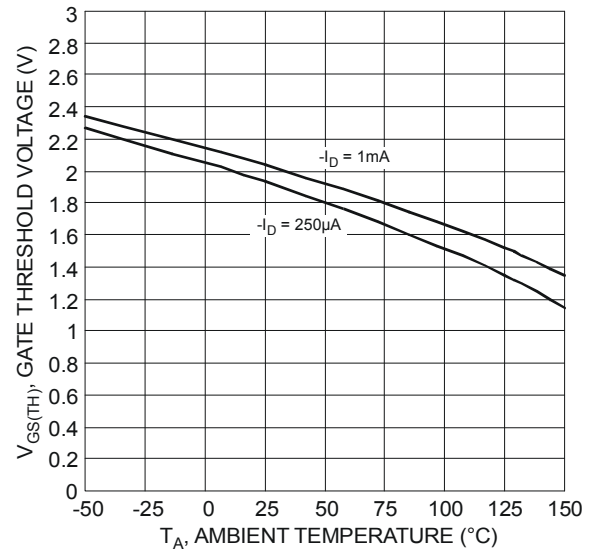
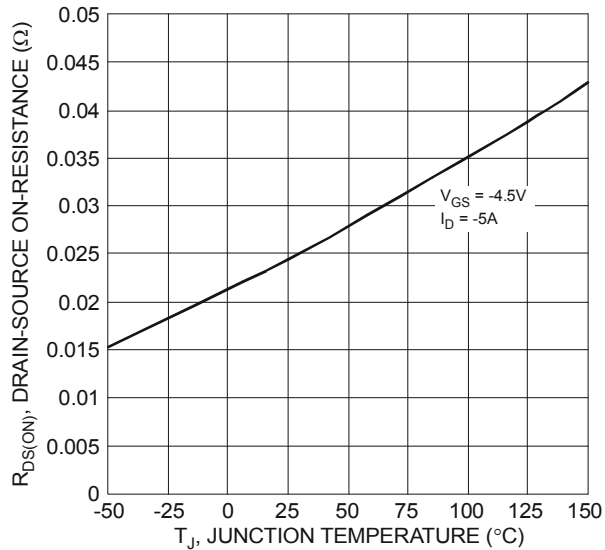
Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	2	W
	T <sub>A</sub> = +70°C		1.3	
Thermal Resistance, Junction to Ambient (Note 5)		R <sub>θJA</sub>	60	°C/W
Total Power Dissipation (Note 5)	T <sub>C</sub> = +25°C	P <sub>D</sub>	17.3	W
Thermal Resistance, Junction to Case (Note 5)		R <sub>θJC</sub>	7.2	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

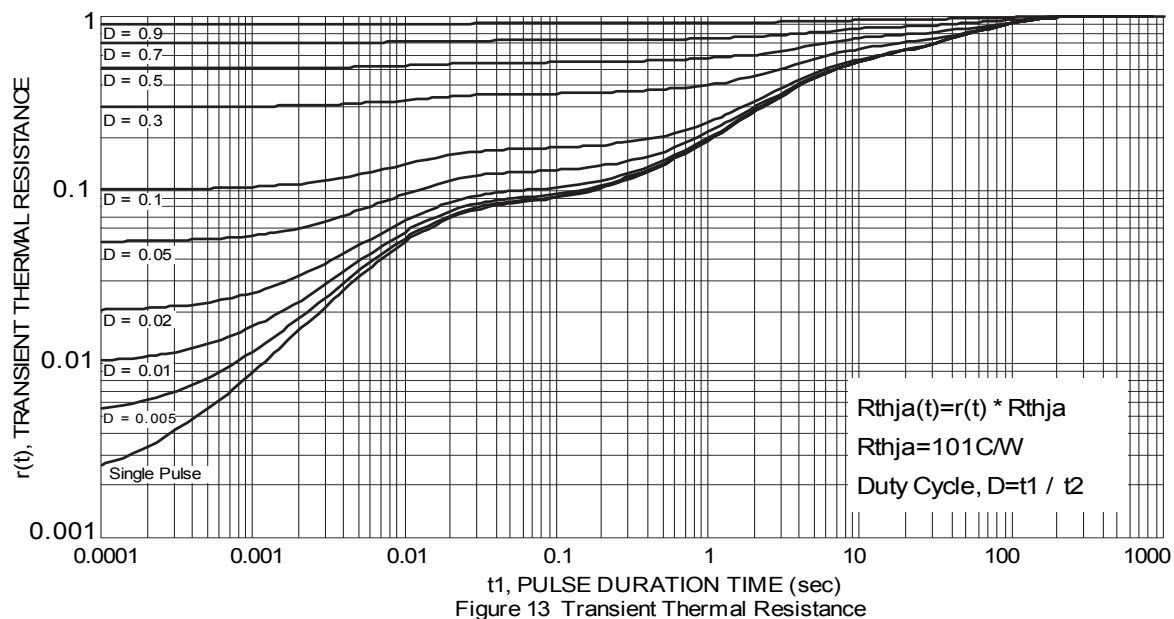
**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 6)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	-1	µA	V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 6)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1	—	-3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250µA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	—	28	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -5A
		—	—	35		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -4A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.7	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A
<b>DYNAMIC CHARACTERISTICS</b> (Note 7)						
Input Capacitance	C <sub>iss</sub>	—	2569	—	pF	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	179	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	143	—	pF	
Gate Resistance	R <sub>g</sub>	—	8	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Q <sub>g</sub>	—	26.5	—	nC	V <sub>DS</sub> = -30V, I <sub>D</sub> = -5A
Total Gate Charge (V <sub>GS</sub> = -10V)	Q <sub>g</sub>	—	53.1	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	7.1	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	12.6	—	nC	
Turn-On Delay Time	t <sub>D(on)</sub>	—	6	—	ns	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -30V, R <sub>G</sub> = 3Ω, I <sub>D</sub> = -5A
Turn-On Rise Time	t <sub>r</sub>	—	7.1	—	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	—	110	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	62	—	ns	
Body Diode Reverse Recovery Time	t <sub>rr</sub>	—	20	—	nS	I <sub>F</sub> = -5A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	—	14	—	nC	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square pad layout.  
6. Short duration pulse test used to minimize self-heating effect.  
7. Guaranteed by design. Not subject to product testing.

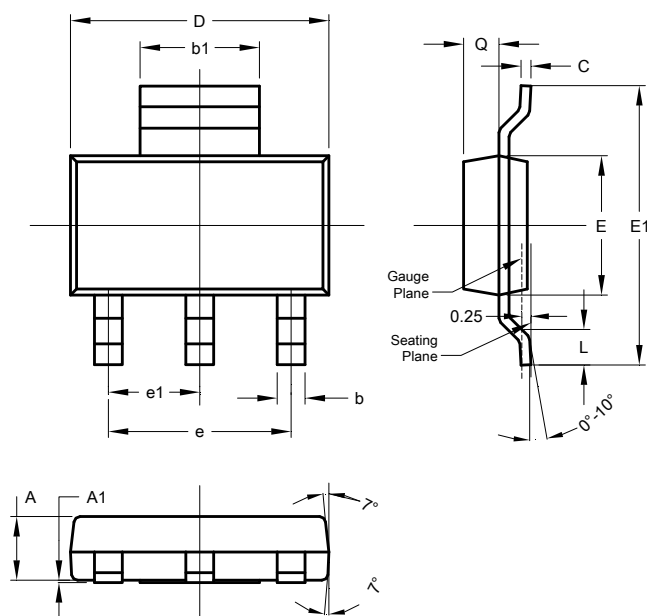






## Package Outline Dimensions

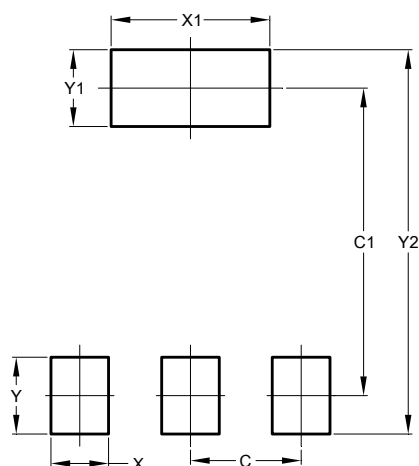
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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